



ZTN23015CFHQ

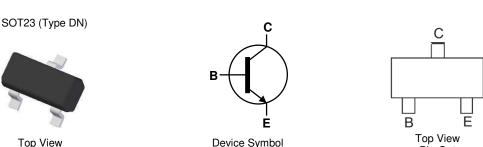
Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirement of Automotive Applications.

Features

- BV_{CEO} > 15V
- Maximum Continuous Collector Current I_C = 6A
- V_{CE(SAT)} < 30mV @ 1A
- R_{CE(SAT)} = 19mΩ Typical
- High Power Dissipation SOT23 Package
- High Peak Current
- Low Saturation Voltage
- 60V Forward Blocking Voltage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The ZTN23015CFHQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/guality/product-definitions/



Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZTN23015CFHQTA	Automotive	327	7	8	3,000

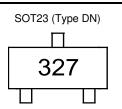
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:



327 = Product Type Marking Code

- Mechanical Data
- Case: SOT23
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0

15V NPN MEDIUM POWER TRANSISTOR IN SOT23

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 2086

 3

Pin-Out

• Weight: 0.008 grams (Approximate)

Applications

- DC DC Converters
- MOSFET and IGBT Gate Driving
- Motor Drive
- Relay, Lamp and Solenoid Drive



Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEV}	60	V
Collector-Emitter Voltage	V _{CEO}	15	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	6	A
Base Current	Ι _Β	1.2	Α
Peak Pulse Current	I _{CM}	12	А

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 6)		0.73 5.84		
Power Dissipation Linear Derating Factor	(Note 7)		1.05 8.4	W mW/°C	
	(Note 8)	PD	1.25 9.6		
	(Note 9)		1.81 14.5		
	(Note 6)		171	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)		119		
	(Note 8)	R _{0JA}	100		
	(Note 9)		69		
Operating and Storage Temperature Range	·	TJ, TSTG	-55 to +150	°C	

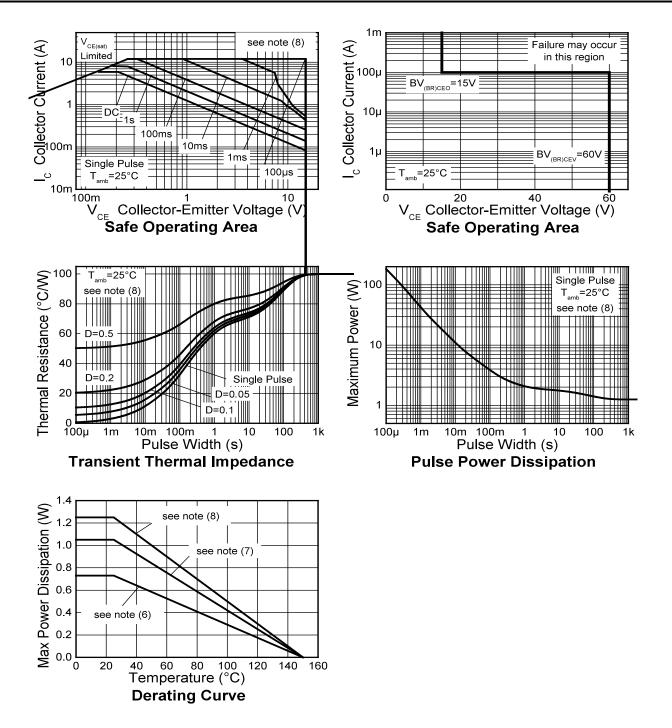
6. For a device mounted with the collector lead on 15mm × 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air Notes: conditions whilst operating in steady-state. 7. Mounted on $25mm \times 25mm 1.6mm FR-4 PCB$ with a high coverage of single sided 2oz copper in still air conditions.

8. Mounted on 50mm × 50mm 1.6mm FR-4 PCB with a high coverage of single sided 2oz copper in still air conditions.

9. Same as note (8), except measured at t < 5 seconds.



Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)





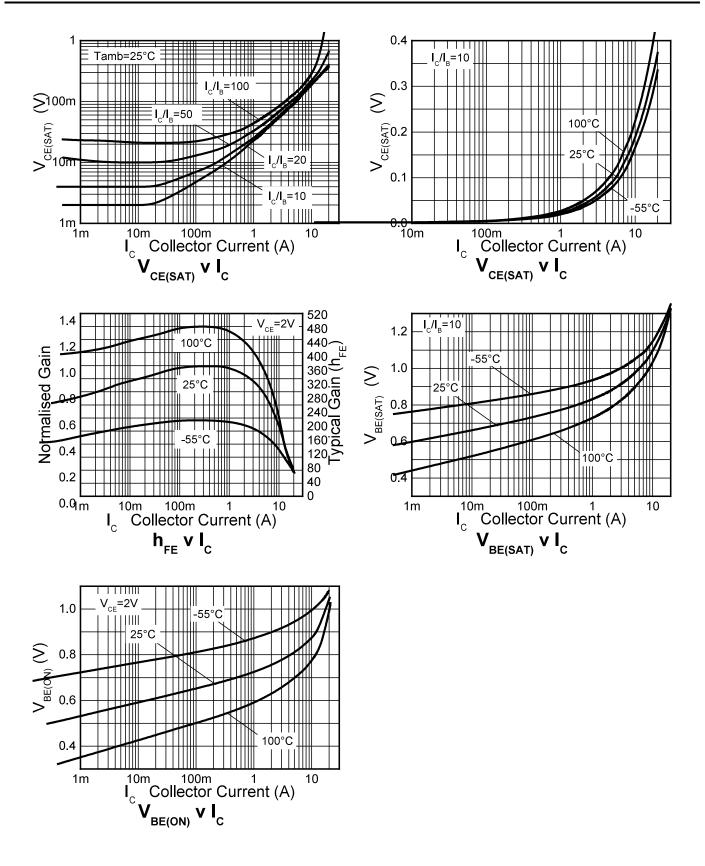
Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	60	85	—	V	I _C = 100μA
Collector-Emitter Breakdown Voltage	BV _{CEV}	60	85	_	V	$I_{C} = 100\mu A$, $R_{BE} \le 1k\Omega$ or -1V < V_{BE} < 0.25V
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	15	23	—	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.3	—	V	I _E = 100μA
Collector-Base Cutoff Current	ICBO	—	< 1	20	nA	V _{CB} = 48V
Collector-Emitter Cutoff Current	I _{CEV}	_	_	100	nA	$V_{CE} = 48V$, $R_{BE} \le 1k\Omega$ or -1V < $V_{BE} < 0.25V$
Emitter-Base Cutoff Current	I _{EBO}	_	< 1	10	nA	$V_{EB} = 6V$
	hFE	160	300	—	_	$I_{C} = 10 \text{mA}, V_{CE} = 2 \text{V}$
Static Forward Current Transfer Ratio (Note 10)		200	350	560		$I_{C} = 500 \text{mA}, V_{CE} = 2 \text{V}$
		190	330	—		$I_C = 3A, V_{CE} = 2V$
		150	280	—		$I_{C} = 6A, V_{CE} = 2V$
	$V_{CE(sat)}$	—	7	15	mV	$I_{C} = 0.1A, I_{B} = 5mA$
Collector-Emitter Saturation Voltage (Note 10)		—	22	30		$I_{C} = 1A, I_{B} = 100mA$
Collector-Emitter Saturation Voltage (Note 10)		_	70	90		$I_{C} = 3A, I_{B} = 60mA$
		—	130	180		$I_{C} = 6A, I_{B} = 120mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	—	0.83	0.93	v	$I_{C} = 3A, I_{B} = 60mA$
Dase-Emilier Saturation Voltage (Note 10)		—	0.89	0.98		$I_{C} = 6A, I_{B} = 120mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(on)}	—	0.81	0.91	V	$I_C = 6A, V_{CE} = 2V$
Output Capacitance	Сово	—	56	—	рF	$V_{CB} = 10V$, f = 1MHz
Transition Frequency	fT	-	235	_	MHz	$V_{CE} = 2V$, $I_C = 500$ mA, f = 50MHz
Delay Time	t _d	—	15	—		
Rise Time	tr	—	38.5	—	ns	$V_{CC} = 5V, I_C = 3A,$
Storage Time	t _{stg}	_	213	—		$I_{B1} = -I_{B2} = 150 \text{mA}$
Fall Time	t _f	—	19.7			

Note: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



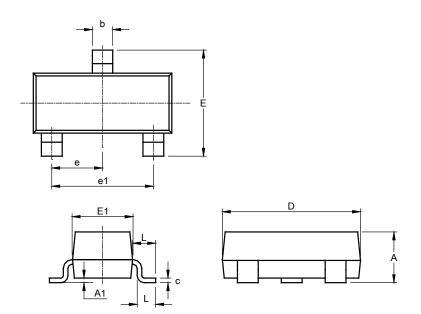
Typical Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

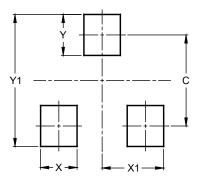
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23 (Type DN)					
Dim	Min	Max	Тур		
Α	0.89	1.12	1.00		
A1	0.01	0.10	0.05		
b	0.30	0.51	0.45		
С	0.08	0.20	0.10		
D	2.80	3.04	3.00		
Е	2.10	2.64	2.42		
E1	1.20	1.40	1.37		
е	0.95 REF				
e1	1.90 REF				
L	0.25	0.60	0.30		
L1	0.45	0.62	0.54		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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